

MOSFETs Silicon N-Channel MOS (DTMOSIV)

# **TK17A65W**

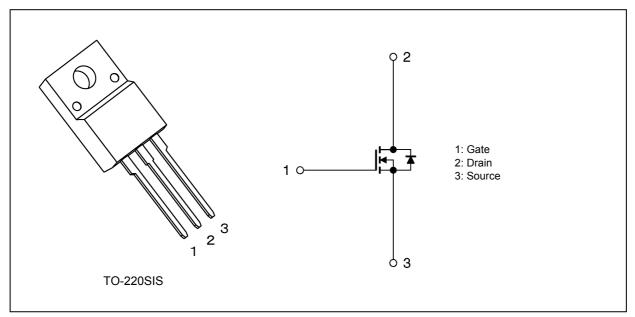
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)}$  = 0.17  $\Omega$  (typ.) by used to Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.5 to 3.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.9 mA)

## 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                | Symbol                  | Rating   | Unit                  |            |       |
|--------------------------------|-------------------------|----------|-----------------------|------------|-------|
| Drain-source voltage           |                         |          | V <sub>DSS</sub>      | 650        | V     |
| Gate-source voltage            |                         |          | V <sub>GSS</sub>      | ±30        |       |
| Drain current (DC)             |                         | (Note 1) | I <sub>D</sub>        | 17.3       | Α     |
| Drain current (pulsed)         |                         | (Note 1) | I <sub>DP</sub>       | 69.2       |       |
| Power dissipation              | (T <sub>c</sub> = 25°C) |          | P <sub>D</sub>        | 45         | W     |
| Single-pulse avalanche energy  |                         | (Note 2) | E <sub>AS</sub>       | 314        | mJ    |
| Avalanche current              |                         |          | I <sub>AR</sub>       | 4.4        | Α     |
| Reverse drain current (DC)     |                         | (Note 1) | I <sub>DR</sub>       | 17.3       |       |
| Reverse drain current (pulsed) |                         | (Note 1) | I <sub>DRP</sub>      | 69.2       |       |
| Channel temperature            |                         |          | T <sub>ch</sub>       | 150        | ℃     |
| Storage temperature            |                         |          | T <sub>stg</sub>      | -55 to 150 |       |
| Isolation voltage (RMS)        | (t = 1.0 s)             |          | V <sub>ISO(RMS)</sub> | 2000       | V     |
| Mounting torque                |                         |          | TOR                   | 0.6        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max  | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 2.78 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 62.5 |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 28.7 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 4.4 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



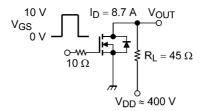
#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|-----|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _    | ±1  | μΑ   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V    | _   | _    | 10  |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 650 | _    | _   | V    |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.9 mA   | 2.5 | _    | 3.5 |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8.7 A    | _   | 0.17 | 0.2 | Ω    |

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1800 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub>   |   | _   | 7    | _   |      |
| Output capacitance             | C <sub>oss</sub>   |   | _   | 40   | _   |      |
| Effective output capacitance   | C <sub>o(er)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V       | _   | 65   | _   |      |
| Gate resistance                | r <sub>g</sub>     | V <sub>DS</sub> = OPEN, f = 1 MHz                         | _   | 1.5  | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>     | See Figure 6.2.1  | _   | 15   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>    |   | _   | 50   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>     |   | _   | 6    | _   |      |
| Switching time (turn-off time) | t <sub>off</sub>   |   | _   | 100  | _   |      |
| MOSFET dv/dt ruggedness        | dv/dt              | V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 8.7 A      | 50  |      |     | V/ns |



Duty  $\leq$  1 %,  $t_{W}=$  10  $\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$            | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 17.3 \text{ A}$ | _   | 45   |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   |     | 11   |     |      |
| Gate-drain charge                               | $Q_{gd}$         |   |     | 20   |     |      |

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition   | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 17.3 A, V <sub>GS</sub> = 0 V                        | _   | _    | -1.7 | V    |
| Reverse recovery time         | t <sub>rr</sub> | I <sub>DR</sub> = 8.7 A, V <sub>GS</sub> = 0 V                         | _   | 300  | _    | ns   |
| Reverse recovery charge       | $Q_{rr}$        | ]-dI <sub>DR</sub> /dt = 50 A/μs                                       |     | 2.7  | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> |  | _   | 16   |      | Α    |
| Diode dv/dt ruggedness        | dv/dt           | $I_{DR} = 8.7 \text{ A}, V_{GS} = 0 \text{ V}, V_{DD} = 400 \text{ V}$ | 15  | _    | _    | V/ns |

## 7. Marking (Note)

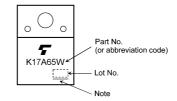


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

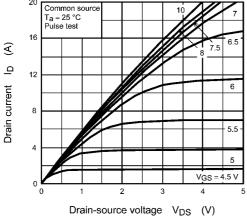
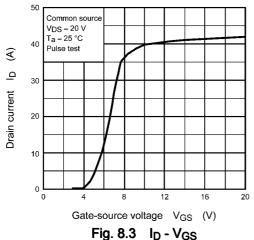


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



rig. 6.5 ip - vgs

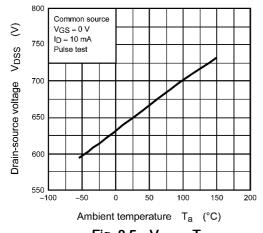


Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

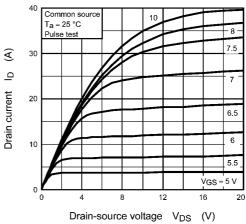


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

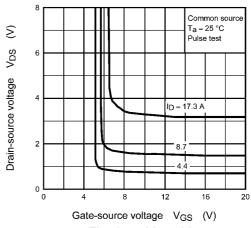


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

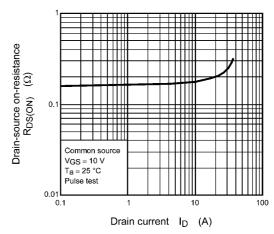


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

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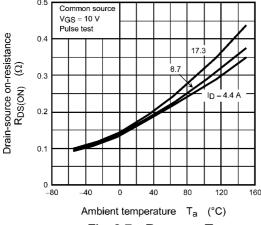


Fig. 8.7 RDS(ON) - Ta

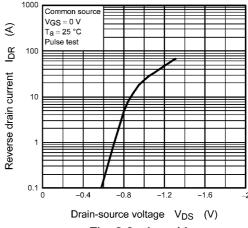


Fig. 8.8 IDR - VDS

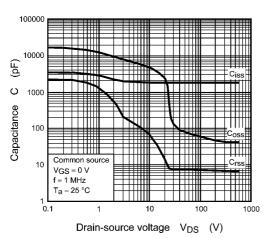


Fig. 8.9 C - V<sub>DS</sub>

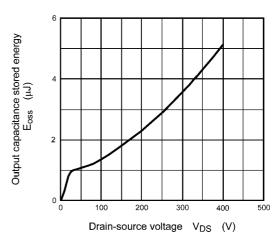


Fig. 8.10 Eoss - VDS

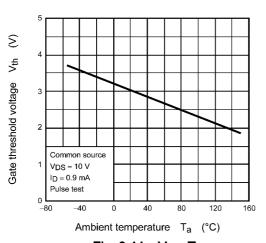


Fig. 8.11 V<sub>th</sub> - T<sub>a</sub>

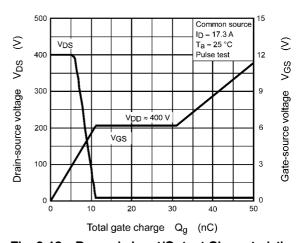


Fig. 8.12 Dynamic Input/Output Characteristics

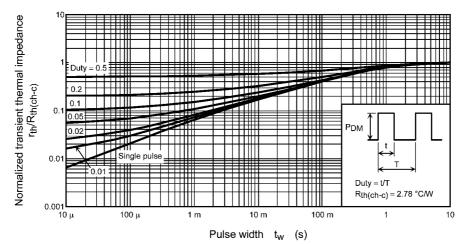


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

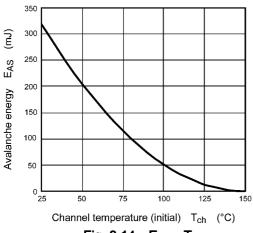


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

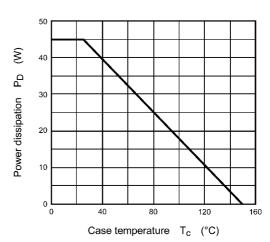


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

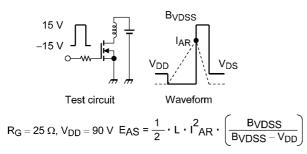


Fig. 8.16 Test Circuit/Waveform

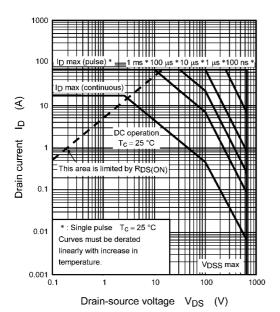


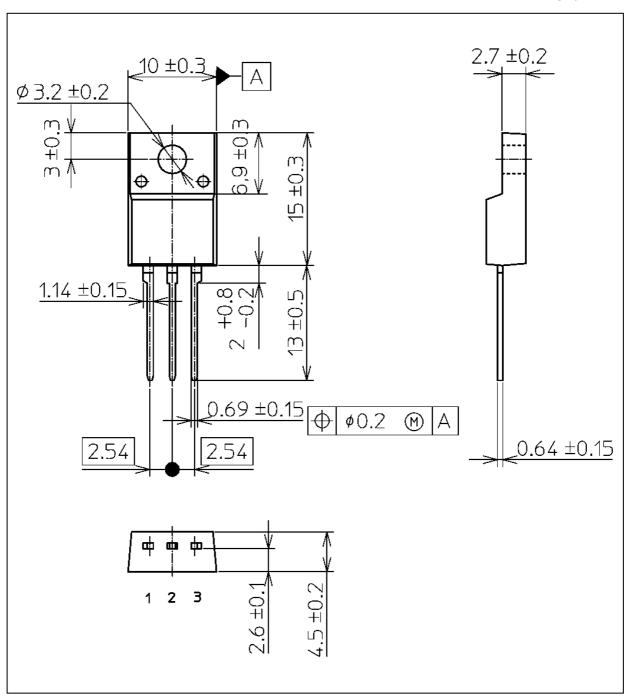
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 1.7 g (typ.)

|                     | Package Name(s) |
|---------------------|-----------------|
| JEITA: SC-67        |                 |
| TOSHIBA: 2-10U1S    |                 |
| Nickname: TO-220SIS |                 |

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